

74AUP1G74-Q100

Low-power D-type flip-flop with set and reset; positive-edge trigger

Rev. 1 — 27 May 2015

Product data sheet

1. General description

The 74AUP1G74-Q100 provides a low-power, low-voltage single positive-edge triggered D-type flip-flop with individual data (D), clock (CP), set (\overline{SD}) and reset (\overline{RD}) inputs and complementary Q and \overline{Q} outputs. The \overline{SD} and \overline{RD} are asynchronous active LOW inputs and operate independently of the clock input. Information on the data input is transferred to the Q output on the LOW-to-HIGH transition of the clock pulse. The D input must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ MIL-STD-883, method 3015 Class 3A. Exceeds 5000 V
 - ◆ HBM JESD22-A114F Class 3A. Exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Low static power consumption; $I_{CC} = 0.9\text{ }\mu\text{A}$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II



- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AUP1G74DC-Q100	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1

4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74AUP1G74DC-Q100	p74

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

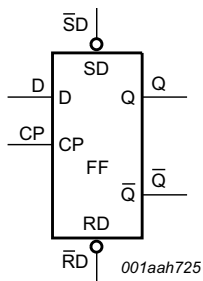


Fig 1. Logic symbol

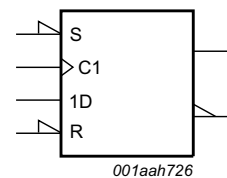


Fig 2. IEC logic symbol

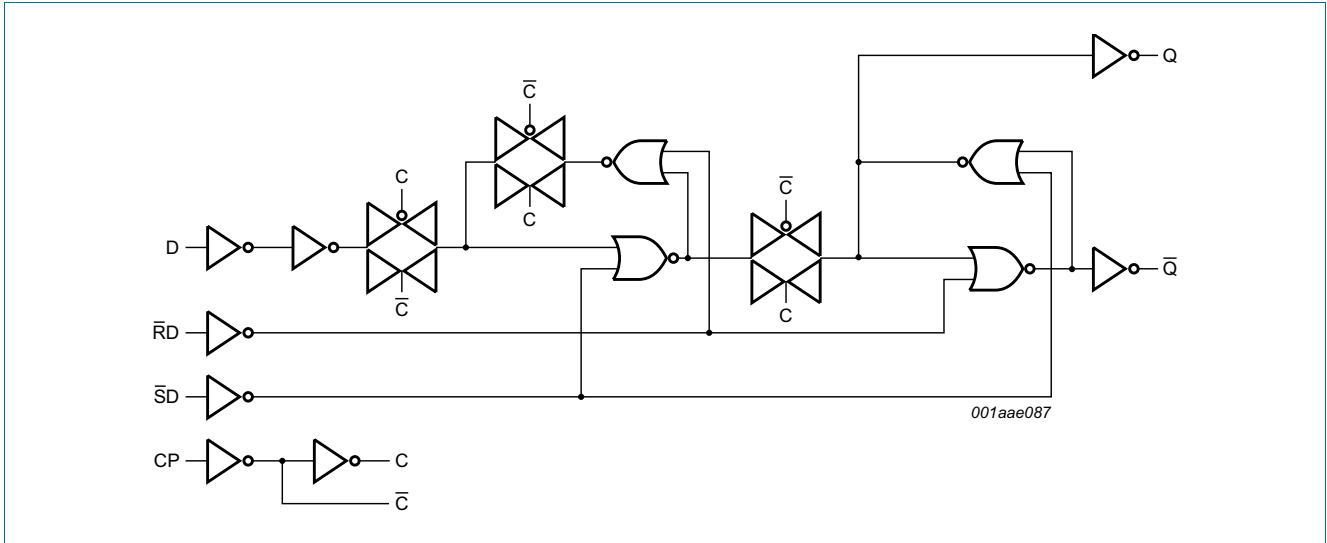


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

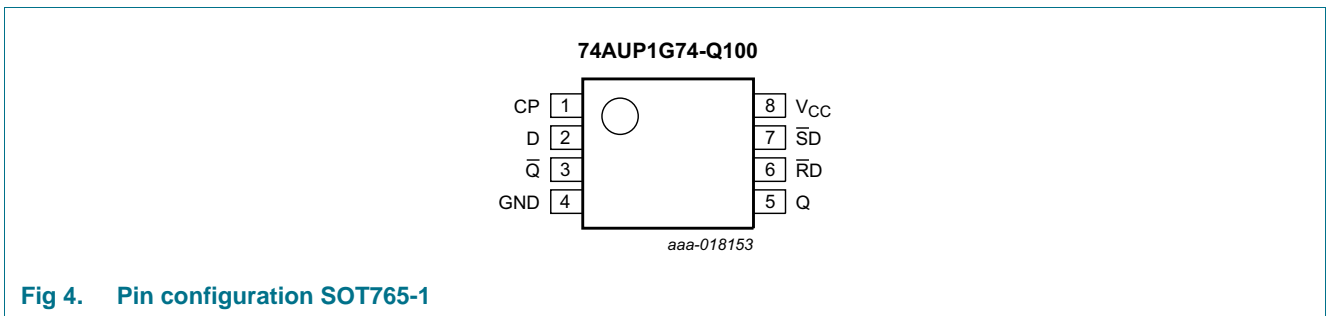


Fig 4. Pin configuration SOT765-1

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
CP	1	clock input
D	2	data input
\bar{Q}	3	complement output
GND	4	ground (0 V)
Q	5	true output
\bar{RD}	6	asynchronous reset input (active LOW)
\bar{SD}	7	asynchronous set input (active LOW)
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table for asynchronous operation^[1]

Input				Output	
SD	$\overline{\text{RD}}$	CP	D	Q	$\overline{\text{Q}}$
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

Table 5. Function table for synchronous operation^[1]

Input				Output	
SD	$\overline{\text{RD}}$	CP	D	Q _{n+1}	$\overline{\text{Q}}_{n+1}$
H	H	↑	L	L	H
H	H	↑	H	H	L

[1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 ↑ = LOW-to-HIGH CP transition;
 Q_{n+1} = state after the next LOW-to-HIGH CP transition.

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
V _O	output voltage	Active mode and Power-down mode	-0.5	+4.6	V
I _O	output current	V _O = 0 V to V _{CC}	-	±20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	-	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.

9. Recommended operating conditions

Table 7. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
V _I	input voltage		0	3.6	V
V _O	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	-	200	ns/V

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V		

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	input leakage current	$V_I = \text{GND to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	± 0.1	μA
I_{OFF}	power-off leakage current	$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	± 0.2	μA
ΔI_{OFF}	additional power-off leakage current	$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	± 0.2	μA
I_{CC}	supply current	$V_I = \text{GND or } V_{CC}; I_O = 0 \text{ A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}; \text{ per pin}$ [1]	-	-	40	μA
C_I	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$	-	0.6	-	pF
C_O	output capacitance	$V_O = \text{GND}; V_{CC} = 0 \text{ V}$	-	1.3	-	pF
$T_{amb} = -40 \text{ }^\circ\text{C to } +85 \text{ }^\circ\text{C}$						
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_O = -20 \text{ } \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	$V_{CC} - 0.1$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_O = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_O = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_O = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_O = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_O = 20 \text{ } \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
I_I	input leakage current	$V_I = \text{GND to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	± 0.5	μA
		$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	± 0.5	μA
		$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	± 0.6	μA

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V; per pin	[1]	-	50	μA
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.40	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	μA
		V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.75	μA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.75	μA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.75	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	1.4	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V; per pin	[1]	-	75	μA

[1] One input at V_{CC} - 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C				Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Min	Max (125 °C)	
C_L = 5 pF										
t _{pd}	propagation delay	CP to Q, \bar{Q} ; see Figure 5 ^[2]								
		V _{CC} = 0.8 V	-	25.4	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.9	6.7	14.0	2.6	14.2	2.6	14.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.4	4.5	7.6	2.3	8.3	2.3	8.6	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	3.5	5.7	1.7	6.5	1.7	6.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	2.6	3.8	1.4	4.4	1.4	4.7	ns
		V _{CC} = 3.0 V to 3.6 V	1.5	2.2	3.1	1.2	3.4	1.2	3.7	ns
		$\bar{S}D$ to Q, \bar{Q} ; see Figure 6 ^[2]								
		V _{CC} = 0.8 V	-	19.6	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.7	5.6	11.0	2.5	11.4	2.5	11.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.4	4.0	6.3	2.2	6.9	2.2	7.3	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.3	4.9	1.7	5.6	1.7	5.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.9	2.7	3.7	1.7	4.0	1.7	4.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.8	2.5	3.2	1.5	3.6	1.5	3.8	ns
		$\bar{R}D$ to Q, \bar{Q} ; see Figure 6 ^[2]								
		V _{CC} = 0.8 V	-	19.2	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.6	5.5	11.0	2.5	11.3	2.5	11.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	3.9	6.3	2.2	6.8	2.2	7.3	ns
V _{CC} = 1.65 V to 1.95 V	1.9	3.2	5.0	1.8	5.6	1.8	5.9	ns		
V _{CC} = 2.3 V to 2.7 V	1.9	2.6	3.6	1.7	4.1	1.7	4.3	ns		
V _{CC} = 3.0 V to 3.6 V	1.8	2.4	3.3	1.5	3.6	1.5	3.8	ns		
f _{max}	maximum frequency	CP; see Figure 5								
		V _{CC} = 0.8 V	-	53	-	-	-	-	MHz	
		V _{CC} = 1.1 V to 1.3 V	-	203	-	170	-	170	-	MHz
		V _{CC} = 1.4 V to 1.6 V	-	347	-	310	-	300	-	MHz
		V _{CC} = 1.65 V to 1.95 V	-	435	-	400	-	390	-	MHz
		V _{CC} = 2.3 V to 2.7 V	-	550	-	490	-	480	-	MHz
		V _{CC} = 3.0 V to 3.6 V	-	619	-	550	-	510	-	MHz

Table 9. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C				Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Min	Max (125 °C)	
C_L = 10 pF										
t _{pd}	propagation delay	CP to Q, \bar{Q} ; see Figure 5 ^[2]								
		V _{CC} = 0.8 V	-	28.9	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.1	7.5	15.8	2.9	16.1	2.9	16.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.7	5.1	8.7	2.4	9.4	2.4	9.8	ns
		V _{CC} = 1.65 V to 1.95 V	2.5	4.1	6.5	2.2	7.2	2.2	7.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	3.2	4.6	1.8	5.3	1.8	5.6	ns
		V _{CC} = 3.0 V to 3.6 V	1.8	2.8	3.8	1.6	4.1	1.6	4.4	ns
		$\bar{S}\bar{D}$ to Q, \bar{Q} ; see Figure 6 ^[2]								
		V _{CC} = 0.8 V	-	23.2	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.9	6.5	12.9	2.8	13.3	2.8	13.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.7	4.6	7.5	2.3	7.9	2.3	8.3	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	3.9	5.6	2.3	6.3	2.3	6.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.3	3.2	4.4	2.0	4.8	2.0	5.2	ns
		V _{CC} = 3.0 V to 3.6 V	2.2	3.0	3.9	1.9	4.2	1.9	4.4	ns
		$\bar{R}\bar{D}$ to Q, \bar{Q} ; see Figure 6 ^[2]								
		V _{CC} = 0.8 V	-	22.7	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.8	6.4	12.8	2.7	13.2	2.7	13.4	ns
		V _{CC} = 1.4 V to 1.6 V	2.6	4.5	7.5	2.3	8.1	2.3	8.4	ns
V _{CC} = 1.65 V to 1.95 V	2.5	3.3	5.8	2.3	6.3	2.3	6.7	ns		
V _{CC} = 2.3 V to 2.7 V	2.2	3.2	4.4	2.0	4.9	2.0	5.2	ns		
V _{CC} = 3.0 V to 3.6 V	2.0	2.9	4.0	1.9	4.3	1.9	4.5	ns		
f _{max}	maximum frequency	CP; see Figure 5								
		V _{CC} = 0.8 V	-	52	-	-	-	-	MHz	
		V _{CC} = 1.1 V to 1.3 V	-	192	-	150	-	150	-	MHz
		V _{CC} = 1.4 V to 1.6 V	-	324	-	280	-	230	-	MHz
		V _{CC} = 1.65 V to 1.95 V	-	421	-	310	-	250	-	MHz
		V _{CC} = 2.3 V to 2.7 V	-	486	-	370	-	360	-	MHz
		V _{CC} = 3.0 V to 3.6 V	-	550	-	410	-	360	-	MHz

Table 9. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C				Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Min	Max (125 °C)	
C_L = 15 pF										
t _{pd}	propagation delay	CP to Q, \bar{Q} ; see Figure 5 ^[2]								
		V _{CC} = 0.8 V	-	32.4	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.5	8.3	17.6	3.3	17.8	3.3	18.0	ns
		V _{CC} = 1.4 V to 1.6 V	3.2	5.6	9.5	2.8	10.5	2.8	11.1	ns
		V _{CC} = 1.65 V to 1.95 V	2.7	4.6	7.2	2.5	8.1	2.5	8.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	3.6	5.2	2.2	5.8	2.2	6.2	ns
		V _{CC} = 3.0 V to 3.6 V	2.2	3.2	4.4	2.0	4.9	2.0	5.2	ns
		$\bar{S}\bar{D}$ to Q, \bar{Q} ; see Figure 6 ^[2]								
		V _{CC} = 0.8 V	-	26.7	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.3	7.3	14.7	3.1	15.2	3.1	15.4	ns
		V _{CC} = 1.4 V to 1.6 V	3.2	5.2	8.3	2.9	9.0	2.9	9.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.8	4.3	6.4	2.5	7.1	2.5	7.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.8	3.7	5.1	2.2	5.5	2.2	5.8	ns
		V _{CC} = 3.0 V to 3.6 V	2.5	3.5	4.6	2.4	5.0	2.4	5.2	ns
		$\bar{R}\bar{D}$ to Q, \bar{Q} ; see Figure 6 ^[2]								
		V _{CC} = 0.8 V	-	26.1	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.2	7.2	14.5	3.1	15.0	3.1	15.2	ns
		V _{CC} = 1.4 V to 1.6 V	3.1	5.1	8.4	2.7	9.2	2.7	9.7	ns
V _{CC} = 1.65 V to 1.95 V	2.7	4.3	6.5	2.6	7.3	2.6	7.7	ns		
V _{CC} = 2.3 V to 2.7 V	2.6	3.6	5.0	2.4	5.5	2.4	5.8	ns		
V _{CC} = 3.0 V to 3.6 V	2.4	3.4	4.6	2.3	5.0	2.3	5.2	ns		
f _{max}	maximum frequency	CP; see Figure 5								
		V _{CC} = 0.8 V	-	50	-	-	-	-	MHz	
		V _{CC} = 1.1 V to 1.3 V	-	181	-	120	-	120	-	MHz
		V _{CC} = 1.4 V to 1.6 V	-	301	-	190	-	160	-	MHz
		V _{CC} = 1.65 V to 1.95 V	-	407	-	240	-	190	-	MHz
		V _{CC} = 2.3 V to 2.7 V	-	422	-	300	-	270	-	MHz
		V _{CC} = 3.0 V to 3.6 V	-	481	-	320	-	300	-	MHz

Table 9. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C				Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Min	Max (125 °C)	
C_L = 30 pF										
t _{pd}	propagation delay	CP to Q, \bar{Q} ; see Figure 5 ^[2]								
		V _{CC} = 0.8 V	-	42.7	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.2	10.6	22.5	4.0	23.0	4.0	23.3	ns
		V _{CC} = 1.4 V to 1.6 V	3.7	7.2	12.0	3.7	13.3	3.7	14.0	ns
		V _{CC} = 1.65 V to 1.95 V	3.5	5.8	9.2	3.4	10.4	3.4	11.0	ns
		V _{CC} = 2.3 V to 2.7 V	3.3	4.7	6.6	3.0	7.3	3.0	7.8	ns
		V _{CC} = 3.0 V to 3.6 V	3.0	4.3	5.8	2.8	6.8	2.8	7.3	ns
		\bar{S} D to Q, \bar{Q} ; see Figure 6 ^[2]								
		V _{CC} = 0.8 V	-	37.0	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.0	9.5	19.8	3.8	20.8	3.8	21.1	ns
		V _{CC} = 1.4 V to 1.6 V	3.8	6.7	10.9	3.7	12.0	3.7	12.7	ns
		V _{CC} = 1.65 V to 1.95 V	3.7	5.6	8.4	3.5	9.3	3.5	9.9	ns
		V _{CC} = 2.3 V to 2.7 V	3.7	4.8	6.6	3.2	7.2	3.2	7.6	ns
		V _{CC} = 3.0 V to 3.6 V	3.4	4.6	6.0	3.1	6.8	3.1	7.1	ns
		\bar{R} D to Q, \bar{Q} ; see Figure 6 ^[2]								
		V _{CC} = 0.8 V	-	36.4	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.9	9.4	19.5	3.8	20.2	3.8	20.5	ns
		V _{CC} = 1.4 V to 1.6 V	3.6	6.6	10.9	3.7	12.0	3.7	12.6	ns
V _{CC} = 1.65 V to 1.95 V	3.5	5.5	8.5	3.5	9.5	3.5	10.1	ns		
V _{CC} = 2.3 V to 2.7 V	3.5	4.7	6.5	3.2	7.1	3.2	7.6	ns		
V _{CC} = 3.0 V to 3.6 V	3.3	4.4	6.1	3.1	7.1	3.1	7.5	ns		
f _{max}	maximum frequency	CP; see Figure 5								
		V _{CC} = 0.8 V	-	28	-	-	-	-	MHz	
		V _{CC} = 1.1 V to 1.3 V	-	145	-	70	-	70	-	MHz
		V _{CC} = 1.4 V to 1.6 V	-	185	-	120	-	110	-	MHz
		V _{CC} = 1.65 V to 1.95 V	-	270	-	150	-	120	-	MHz
		V _{CC} = 2.3 V to 2.7 V	-	290	-	190	-	170	-	MHz
		V _{CC} = 3.0 V to 3.6 V	-	315	-	200	-	190	-	MHz

Table 9. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C				Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Min	Max (125 °C)	
C_L = 5 pF, 10 pF, 15 pF and 30 pF										
t _{su}	set-up time	D to CP HIGH; see Figure 5								
		V _{CC} = 0.8 V	-	3.4	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	-	0.6	-	1.2	-	1.2	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	0.3	-	0.6	-	0.6	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	0.4	-	0.5	-	0.5	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	0.2	-	0.4	-	0.4	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	0.3	-	0.4	-	0.4	-	ns
		D to CP LOW; see Figure 5								
		V _{CC} = 0.8 V	-	3.0	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	-	0.5	-	1.2	-	1.2	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	0.3	-	0.7	-	0.7	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	0.4	-	0.7	-	0.7	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	0.5	-	0.7	-	0.7	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	0.6	-	0.8	-	0.8	-	ns
t _h	hold time	D to CP; see Figure 5								
		V _{CC} = 0.8 V	-	-1.9	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	-	-0.3	-	0.5	-	0.5	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	-0.2	-	0.2	-	0.2	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	-0.2	-	0.1	-	0.1	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	-0.2	-	0.1	-	0.1	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	-0.2	-	0.1	-	0.1	-	ns
t _{rec}	recovery time	\overline{RD} ; see Figure 6								
		V _{CC} = 1.1 V to 1.3 V	-	-0.5	-	-0.9	-	-0.9	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	-0.2	-	-0.6	-	-0.6	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	-0.2	-	-0.4	-	-0.4	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	-0.1	-	-0.1	-	-0.1	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	-0.1	-	-0.1	-	-0.1	-	ns
		\overline{SD} ; see Figure 6								
		V _{CC} = 1.1 V to 1.3 V	-	-0.5	-	-0.3	-	-0.3	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	-0.4	-	-0.1	-	-0.1	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	-0.3	-	0	-	0	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	-0.2	-	0.1	-	0.1	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	-0.1	-	0.1	-	0.1	-	ns

Table 9. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C				Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Min	Max (125 °C)	
t _w	pulse width	CP HIGH or LOW; see Figure 5								
		V _{CC} = 1.1 V to 1.3 V	-	2.1	-	2.7	-	2.7	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	1.1	-	1.5	-	1.5	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	0.9	-	1.6	-	1.6	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	0.6	-	1.7	-	1.7	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	0.6	-	1.9	-	1.9	-	ns
		\overline{SD} or \overline{RD} LOW; see Figure 6								
		V _{CC} = 1.1 V to 1.3 V	-	4.2	-	11.3	-	11.5	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	2.3	-	6.2	-	6.4	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	1.8	-	4.8	-	5.0	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	1.2	-	3.3	-	3.5	-	ns
V _{CC} = 3.0 V to 3.6 V	-	1.1	-	2.6	-	2.8	-	ns		
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC} ^[3]								
		V _{CC} = 0.8 V	-	2.8	-	-	-	-	pF	
		V _{CC} = 1.1 V to 1.3 V	-	2.9	-	-	-	-	pF	
		V _{CC} = 1.4 V to 1.6 V	-	3.0	-	-	-	-	pF	
		V _{CC} = 1.65 V to 1.95 V	-	3.0	-	-	-	-	pF	
		V _{CC} = 2.3 V to 2.7 V	-	3.5	-	-	-	-	pF	
		V _{CC} = 3.0 V to 3.6 V	-	3.9	-	-	-	-	pF	

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 Σ(C_L × V_{CC}² × f_o) = sum of outputs.

12. Waveforms

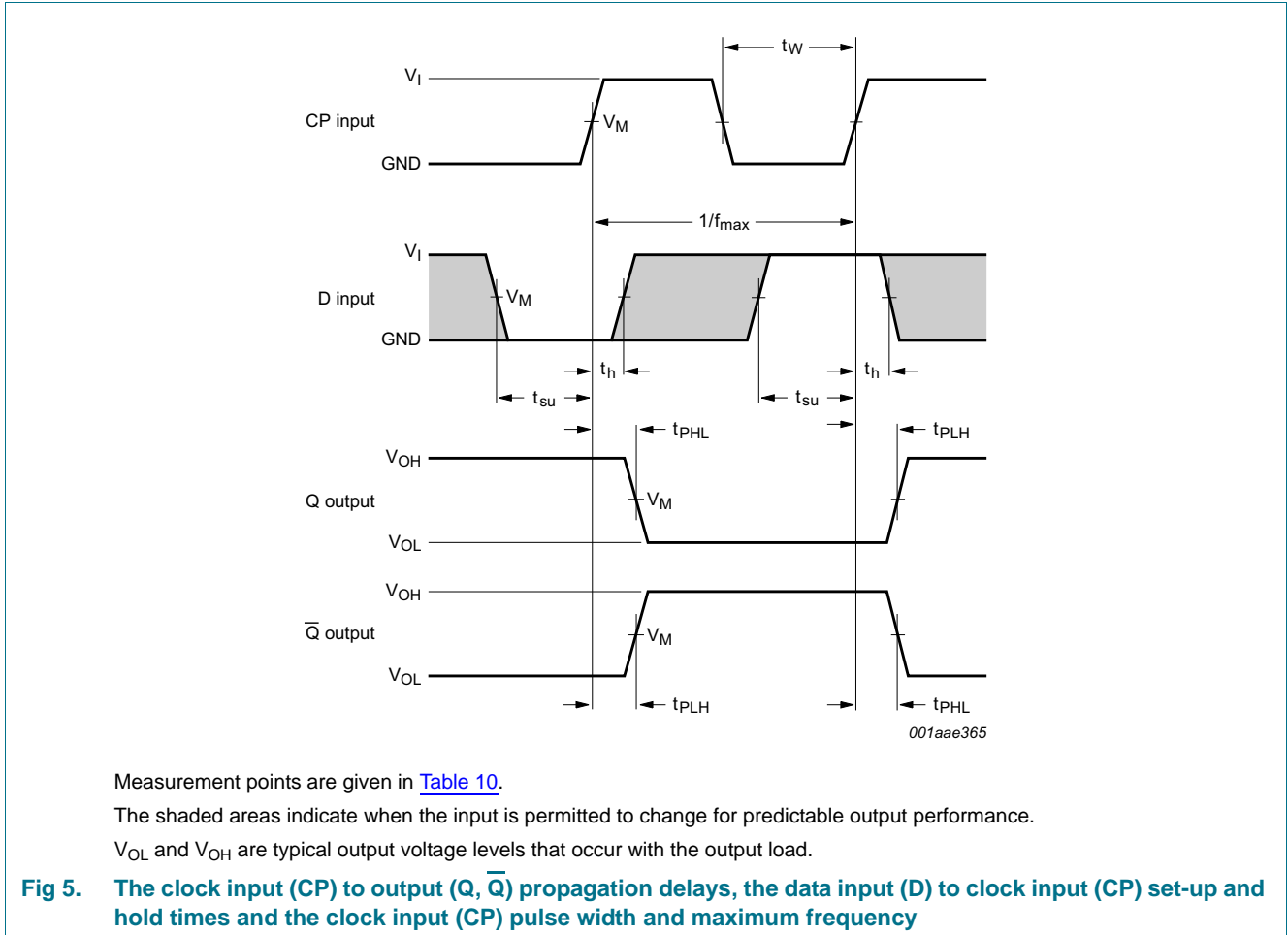
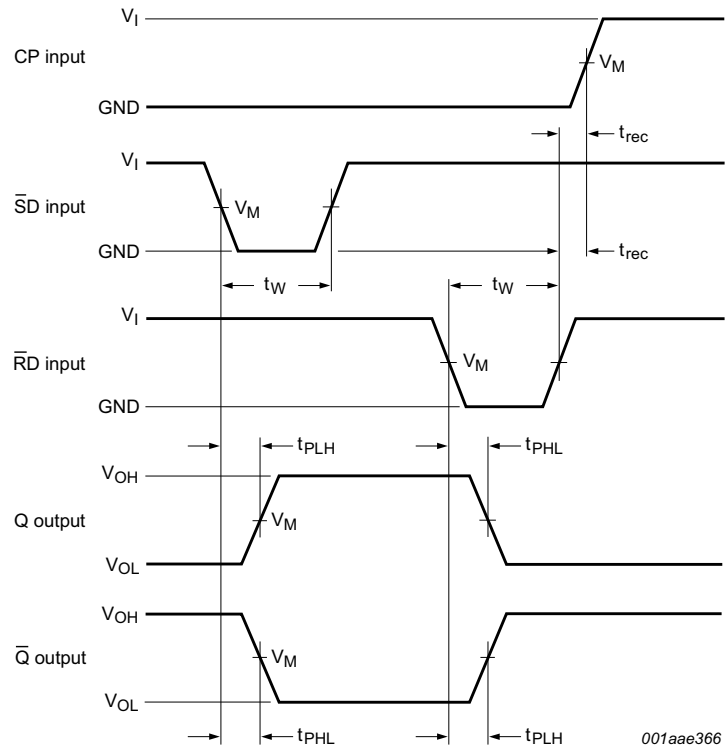


Table 10. Measurement points

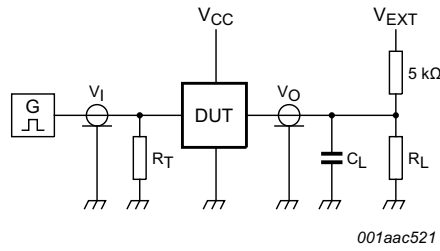
Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_I	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{CC}	≤ 3.0 ns



Measurement points are given in [Table 10](#).

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. The set input ($\bar{S}D$) and reset input ($\bar{R}D$) to output (Q , \bar{Q}) propagation delays, the set input ($\bar{S}D$) and reset input ($\bar{R}D$) pulse widths and the reset input ($\bar{R}D$) to clock input (CP) recovery time



001aac521

Test data is given in [Table 11](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 7. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L [1]	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$

For measuring propagation delays, setup and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

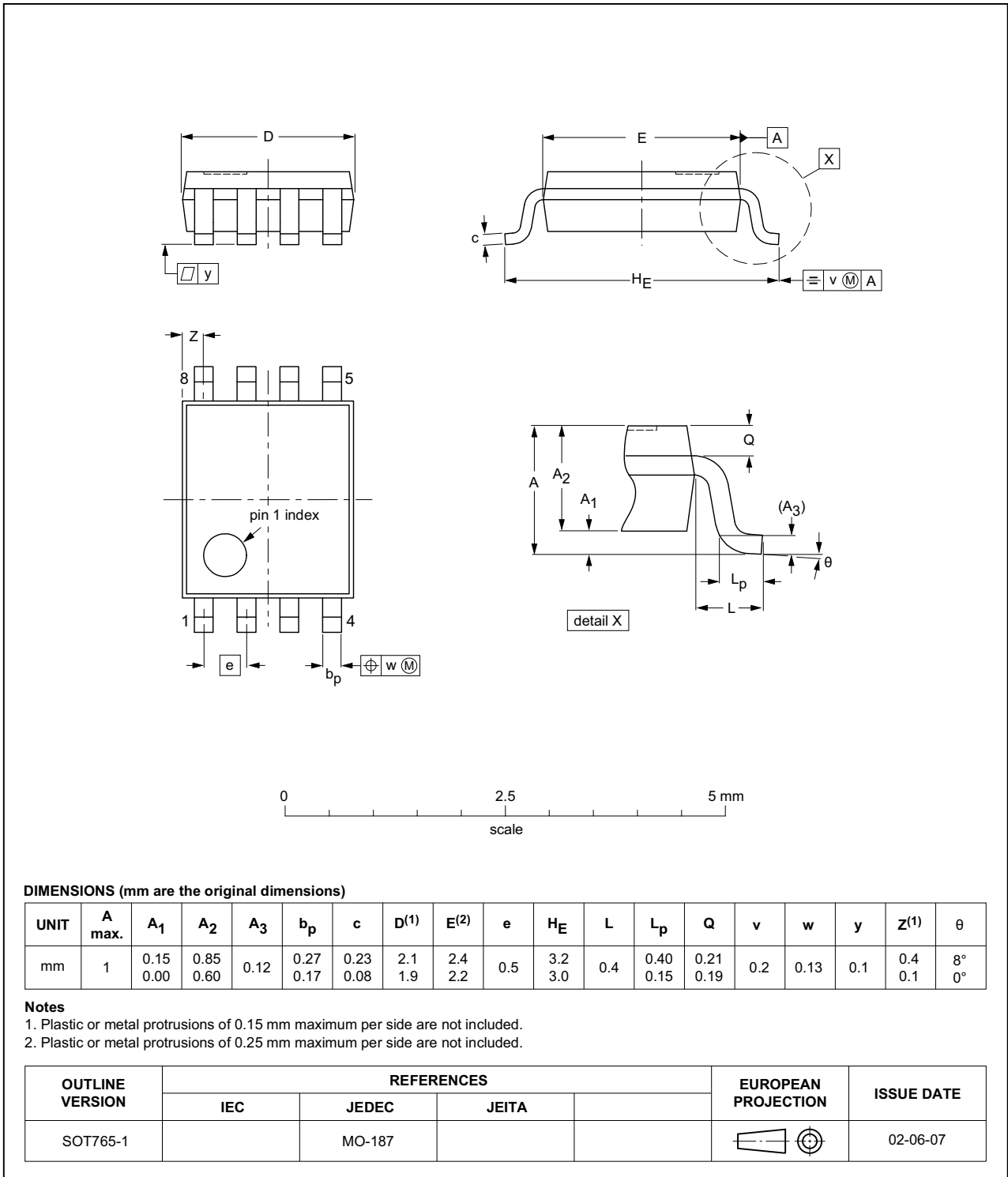


Fig 8. Package outline SOT765-1 (VSSOP8)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G74_Q100 v.1	20150527	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331